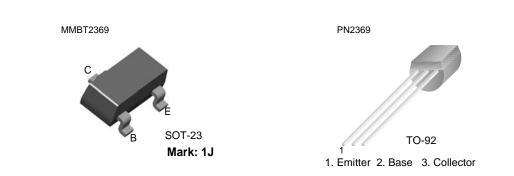


MMBT2369 / PN2369 NPN Switching Transistor

- This device is designed for high speed saturated switching at collector currents of 10mA to 100mA.
- Sourced from process 21.



Absolute Maximum Ratings * T_a = 25xC unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{CEO}	Collector-Emitter Voltage	15	V	
V _{CBO}	Collector-Base Voltage	40	V	
V _{EBO}	Emitter-Base Voltage	4.5	V	
I _C	Collector Current - Continuous	200	mA	
I _{CP}	P **Collector Current (Pulse)		mA	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 ~ 150	°C	

* This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

** Pulse Test: Pulse Width £ 300ms, Duty Cycle £ 2.0%

NOTES:

1) These rating are based on a maximum junction temperature of 150 degrees C.

2) These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

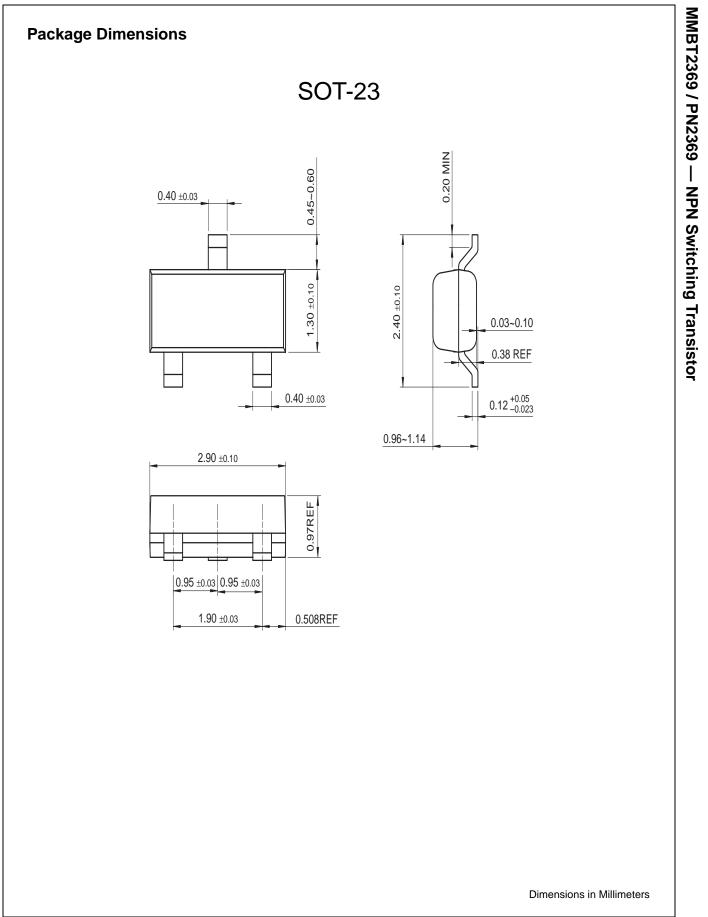
Thermal Characteristics $T_a = 25^{\circ}C$ unless otherwise noted

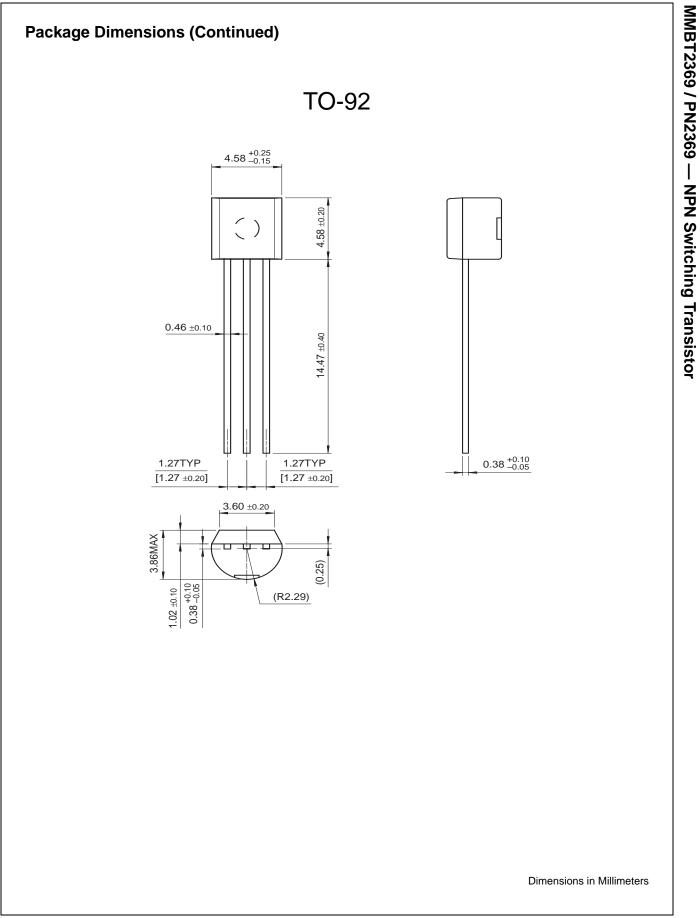
Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
R _{0JA} Thermal Resistance, Junction to Ambient		357	°C/W

* Device mounted on FR-4PCB 1.6" ¥ 1.6" ¥ 0.06".

MMBT2369 /
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Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Charact	eristics				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage *	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$	15		V
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	$I_{C} = 10 \mu A, V_{BE} = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \mu {\rm A}, I_{\rm E} = 0$	40		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \mu {\rm A}, I_{\rm C} = 0$	4.5		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 20V, I_E = 0$ $V_{CB} = 20V, I_E = 0, T_a = 125^{\circ}C$		0.4 30	μΑ μΑ
On Charact	eristics				
h _{FE}	DC Current Gain *	$I_{C} = 10mA, V_{CE} = 1.0V$ $I_{C} = 100mA, V_{CE} = 2.0V$	40 20	120	
V _{CE(sat)}	Collector-Emitter Saturation Voltage *	I _C = 10mA, I _B = 1.0mA		0.25	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 10mA, I _B = 1.0mA	0.7	0.85	V
Small Signa	al Characteristics				
C _{obo}	Output Capacitance	$V_{CB} = 5.0V, I_E = 0, f = 1.0MHz$		4.0	pF
C _{ibo}	Input Capacitance	$V_{EB} = 0.5 V$, $I_C = 0$, $f = 1.0 MHz$		5.0	pF
h _{fe}	Small -Signal Current Gain	I_{C} = 10mA, V_{CE} = 10V, R_{G} = 2.0k Ω , f = 100MHz	5.0		
Switching C	Characteristics				
t _s	Storage Time	$I_{B1} = I_{B2} = I_C = 10 \text{mA}$		13	ns
t _{on}	Turn-On Time	$V_{CC} = 3.0V, I_{C} = 10mA, I_{B1} = 3.0mA$		12	ns
t _{off}	Turn-Off Time	$V_{CC} = 3.0V, I_C = 10mA, I_{B1} = 3.0mA,$ $I_{B2} = 1.5mA$		18	ns







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